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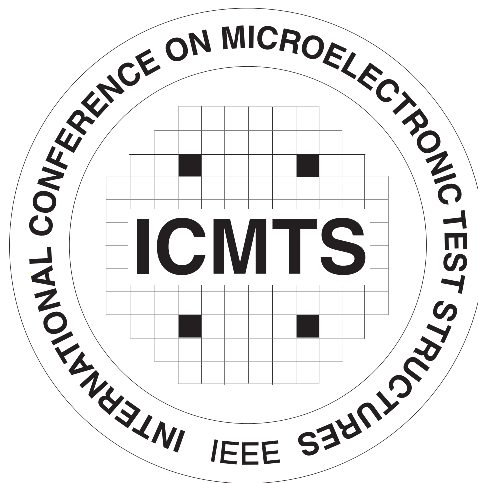
International Conference on
Microelectronic Test Structures



Conference Proceedings
March 24-27
The University of Edinburgh, UK

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WELCOME LETTER

Dear Colleagues

The 2008 IEEE International Conference on Microelectronic Test Structures (ICMTS) will be held at the University of Edinburgh, which recently celebrated its 400th anniversary. ICMTS has come of age and this meeting celebrates its 21st anniversary by visiting Edinburgh for the second time. The conference is being run in cooperation with the University of Edinburgh and the Scottish Microelectronics Centre. As was the case for the first ICMTS conference, it is is being sponsored by the IEEE Electron Devices Society, and for the first time the meeting is also being technically co-sponsored by the IEEE Solid State Circuits Society.

The first ICMTS was held in Long Beach in 1988, and since then the conference has cycled between Europe, North America, and Asia. Over the past twenty one years it has brought together designers and users of test structures to discuss recent developments and future directions. As in previous years the conference will be preceded by a one-day Tutorial Short Course on microelectronic test structures and there will also be a related equipment exhibition focused on test structure measurements. We are very fortunate to be holding the conference banquet in the Playfair Library. Its eleven bays of books supporting a coffered vaulted ceiling make it one of Edinburgh's grandest interiors. The conference will be held at the Appleton Tower in the University of Edinburgh, which is located close the heart of Scotland's capital city.

With its stunning Georgian and Victorian architecture, and winding medieval streets, it's easy to see why Edinburgh has been listed as a World Heritage Site. Edinburgh has one of the most beautiful cityscapes in the world with the famous castle perched atop the crags of an ancient volcano dominating the urban skyline. At the opposite end of "The Royal Mile" lies the Palace of Holyrood. This is the Queen's official residence in Scotland and contains historic apartments where Mary, Queen of Scots lived. The capital is bustling with arts, culture, sports and attractions and is famous for playing host to the world's largest arts festival. The city is the birthplace of James Clerk Maxwell, Sir Arthur Conan Doyle, author of the Sherlock Holmes novels and Alexander Graham Bell, inventor of the telephone. After dark, Edinburgh has a lively nightlife with stylish bars and pubs, restaurants, clubs and live entertainment to rival any European City. We are sure that everyone will enjoy attending the various sessions that make up ICMTS and derive great benefit from the numerous networking opportunities. We look forward to welcoming you to Edinburgh.

Sincerely

Anthony Walton, General Chairman
Jurriaan Schmitz, Technical Chair
Stewart Smith, Conference Vice Chair

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